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SHEET 1 OF 2

FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.: GR99P3456 Appl. No. Applicant HARALD KUHN ET AL. Filing Date January 7, 2002 Group Art Unit			
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EXAMINER INITIALS	PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
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		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J ✓	32 30 727 A1	2/23/84	Germany			
	K ✓	32 30 727 C2	2/23/84	Germany			
	L ✓	0 389 533 B1	10/3/90	Europe			
	M ✓	09 142 995 A	6/3/97	Japan			
	N ✓	10 182 296 A	7/7/98	Japan			

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)	
	✓ Yoo, W. et al.: "Bulk Crystal Growth of 6H-SiC on Polytype-Controlled Substrates Through Vapor Phase and Characterization", Elsevier Science Publishers B.V., 1991, pp. 733-739; <i>no month</i>
	✓ Takahashi, J. et al.: "Influence of the Seed Face Polarity on the Sublimation Growth of α -SiC", Jpn. J. Appl. Phys., Vol. 34, Part 1, No. 9A, September 1995, pp. 4694-4698; <i>no month</i>

EXAMINER:	DATE CONSIDERED: <i>10/29/03</i>
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SHEET 2 OF 2

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DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES	TRANSL. NO
MAA J ✓ 11 060 390	3/2/99	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	Jayatirtha, H. et al.: "Improvement in the Growth Rate of Cubic Silicon Carbide Bulk Single Crystals grown by the sublimation Method", Elsevier Science B.V., 1997, pp. 662-668; <i>no note</i>
	Ohtani, N. et al.: "Development of Large Single-Crystal SiC Substrates", Scripta Technica, 1998, pp. 8-17; <i>no note</i>

EXAMINER <i>Matthew Cluden</i>	DATE CONSIDERED <i>10/29/03</i>
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